

General Description

The AAT8541 is a low threshold MOSFET designed for the battery, cell phone, and PDA markets. Using AnalogicTech™'s ultra high density MOSFET process and space saving small outline J-lead package, performance superior to that normally found in a TSOP-6 footprint has been squeezed into the footprint of a SC70 package.

Features

- $V_{DS(MAX)} = -20V$ $I_{D(MAX)}^{1} = -3.0A @ 25^{\circ}C$
- Low $R_{DS(ON)}$:

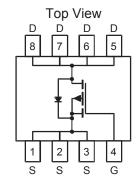
 100 mΩ @ V_{GS} = -4.5V

 175 mΩ @ V_{GS} = -2.5V

SC70JW-8 Package

Applications

- **Battery Packs**
- Cellular & Cordless Telephones
- Battery-powered portable equipment



Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Description		Value	Units	
V _{DS}	Drain-Source Voltage		-20	V	
V_{GS}	Gate-Source Voltage		±12	, v	
I _D	Continuous Drain Current @ T _J =150°C ¹	T _A = 25°C	±3.0		
		T _A = 70°C	±2.4	Α	
I _{DM}	Pulsed Drain Current ²		±12		
I _S	Continuous Source Current (Source-Drain Diode) 1		-1.1		
P _D	Maximum Power Dissipation ¹	T _A = 25°C	1.5	W	
		T _A = 70°C	0.9	V V	
T _J , T _{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C	

Thermal Characteristics

Symbol	Description	Тур	Max	Units	
$R_{\theta JA}$	Junction-to-Ambient steady state 1	107	130	°C/W	
$R_{\theta JA2}$	Junction-to-Ambient t<5 seconds 1	68	83	°C/W	
$R_{\theta JF}$	Junction-to-Foot 1	40	48	°C/W	

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Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Description	Conditions	Min	Тур	Max	Units
DC Charac	DC Characteristics					'
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20			V
R _{DS(ON)}	Drain-Source ON-Resistance ²	V _{GS} =-4.5V, I _D =-3.0A		80	100	mΩ
		V_{GS} =-2.5V, I_{D} =-2.3A		140	175	7 11152
I _{D(ON)}	On-State Drain Current ²	V_{GS} =-4.5V, V_{DS} =-5V (Pulsed)	-12			Α
V _{GS(th)}	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_{D}=-250\mu A$	-0.6			V
I _{GSS}	Gate-Body Leakage Current	V_{GS} =±12V, V_{DS} =0V			±100	nA
I _{DSS}	Drain Source Leakage Current	V _{GS} =0V, V _{DS} =-20V			-1	
		V _{GS} =0V, V _{DS} =-16V, T _J =70°C ³			-5	- μA
9 _{fs}	Forward Transconductance ²	V_{DS} =-5V, I_{D} =-3.0A		4		S
Dynamic C	Dynamic Characteristics ³					
Q_G	Total Gate Charge	V_{DS} =-15V, R_{D} =5 Ω , V_{GS} =-4.5V		4.2		
Q_{GS}	Gate-Source Charge	V_{DS} =-15V, R_{D} =5 Ω , V_{GS} =-4.5V		0.7		nC
Q_{GD}	Gate-Drain Charge	V_{DS} =-15V, R_{D} =5 Ω , V_{GS} =-4.5V		1.7		
t _{D(ON)}	Turn-ON Delay	V_{DS} =-15V, R_{D} =5 Ω , V_{GS} =-4.5V, R_{G} =6 Ω		TBD		
t_R	Turn-ON Rise Time	V_{DS} =-15V, R_{D} =5 Ω , V_{GS} =-4.5V, R_{G} =6 Ω		TBD		ns
t _{D(OFF)}	Turn-OFF Delay	V_{DS} =-15V, R_{D} =5 Ω , V_{GS} =-4.5V, R_{G} =6 Ω		TBD		115
t _F	Turn-OFF Fall Time	V_{DS} =-15V, R_D =5 Ω , V_{GS} =-4.5V, R_G =6 Ω		TBD		
Source-Drain Diode Characteristics						
V_{SD}	Source-Drain Forward Voltage ²	V _{GS} =0, I _S =-3.0A			-1.3	V
Is	Continuous Diode Current ¹				-1.1	Α

Note 1: Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 5 second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications. $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$ where the foot thermal reference is defined as the normal solder mounting surface of the device's leads. $R_{\theta JF}$ is guaranteed by design, however $R_{\theta CA}$ is determined by the PCB design. Actual maximum continuous current is limited by the application's design.

Note 2: Pulse test: Pulse Width = 300 μ s

Note 3: Guaranteed by design. Not subject to production testing.

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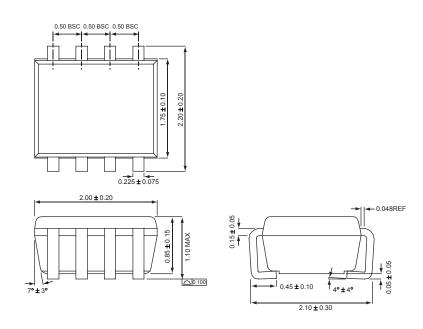


Ordering Information

Package	Marking	Part Number (Tape and Reel)
SC70JW-8		AAT8541IJS-T1

Package Information

SC70JW-8



All dimensions in millimeters.

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